Possible evidence of a spontaneous spin-polarization in mesoscopic 2D electron systems

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We have experimentally studied the non-equilibrium transport in low-density clean 2D electron systems at mesoscopic length scales. At zero magnetic field (B), a double-peak structure in the non-linear conductance was observed close to the Fermi energy in the localized regime. From the behavior of these peaks at non-zero B, we could associate them to the opposite spin states of the system, indicating a spontaneous spin polarization at B = 0. Detailed temperature and disorder dependence of the structure shows that such a splitting is a ground state property of the low-density 2D systems.

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Spin polarization of electrons in low dimensional systems at B = 0 has recently attracted extensive theoretical and experimental attention. In the metallic regime, this is commonly attributed to the spin-orbit (SO) effect, where the bulk inversion asymmetry (the k^3 term) and the interface inversion asymmetry (the Rasba term) result in an energy separation of several millivolts between the spin bands in narrow band semiconductors [1]. At low electron densities however, the electron-electron interaction dominates over the kinetic energy, and a homogeneous 2D system becomes unstable to spontaneous spin polarization (SSP) due to exchange [2, 3]. Since the influence of interaction is strong at lower dimensions, several recent experimental investigations on the spin state of 0D [4, 5] and 1D systems [6] have indicated the possibility of a SSP, even though the origin and nature of such a phase is controversial. In low-density 2D electron systems (2DES's), however, a direct observation of a "spin gap" has remained experimentally illusive, even though evidence of an enhanced g-factor and anomalous spin-susceptibility have been reported when the disorder is low [7, 8, 9, 10].

It is now known that, an unpaired spin in weakly-isolated systems are screened by Kondo-like singlet formation with the electrons in the leads [11]. This results in a resonance in the tunnelling density-of-states (DOS), and an enhancement in the differential conductance (dI=dV) through the system when the chemical potential of the leads are aligned. When studied as a function of source-drain bias (V_{SD}), the zero-bias peak (ZBP) splits linearly in finite B by $_Z = g\ _B B$, where g and $_B$ are the effective g-factor and the Bohr magneton respectively. Recent non-linear studies in ballistic quantum point contacts (QPC's) have also shown the evidence of a ZBP [12], which was attributed to a Kondo-like correlation resulting from a dynamic SSP in 1D. In this Letter, we report the direct observation of SSP in low-density 2DES's. High quality 2DES's of mesoscopic length scales were used with no intentional in-plane confinements. In the localized regime, clear evidence of a split ZBP was observed at B = 0. The magnitude of the split ( ) evolved continuously with B, implying its origin to be related to the underlying spin structure of the 2DES. Simultaneous measurement of the Fermi energy (E_F) showed that such a polarization is an intrinsic ground state property of 2D systems, and depends critically on the impurity scattering, as well as the temperature (T) and magnetic field (B).

We have used 2DES's confined to the triangular potential wells of Si -doped GaAs/AlGaAs heterostructures. In most samples, the 2DES's were formed 300 nm below the surface. Disorder was varied by changing the spacer thickness $_{sp}$ separating the dopant layer from the GaAs/AlGaAs interface. Data from two samples with $_{sp}$ = 40 nm and 60 nm (referred as A78 and A79, respectively) are reported in this work, even though all the samples show qualitatively similar results. In both samples, a source-drain voltage V_{SD} was applied on a 5 m 5 m region of the wafer, defined by an etched mesa and a metallic surface gate. At zero gate voltage (V_g = 0) the mobility of both samples were & 2 10^6 cm^2/V-sec. Lifetime measurements confirm the dominance of the small angle scattering. By varying V_g, electron density (n_s) as low as 5 10^8 cm^{-2} could be attained in sample A79 (corresponding to an interaction parameter $r_s = 1/a_B \sqrt{n_s}$ 7.6, where a_B is the effective Bohr radius). In all the magnetic field measurements, B was applied in the plane of the 2DES and parallel to the direction of the current. The differential conductance dI=dV was measured with a standard 2-probe mixed ac-dc method, where the ac excitation bias was kept at < $k_B T/e$. For all samples, the gate was trained several hundred times to obtain an excellent run to run reproducibility (better than 0.1%).

Dependence of the linear response conductance (G) on V_g is shown in Fig. 1 at various values of B, recorded at T 35 mK in sample A79. We focus on the localized regime (MIT in A79 occurs at G 3 e^2/h), where the electron density is low, and the interaction effects are most pronounced. For all V_g, G was found to decrease

rapidly with increasing B. The functional dependence of the in plane magneto-conductance (MC) on B has been shown to change from e^{B^2} to e^{B} at a critical field B_c, when the electron gas becomes completely spin polarized, and the majority and minority spin bands are separated by the Fermi energy [7, 10]. In the inset of Fig. 1 we have shown the zero-bias MC as a function of B^2 at four representative gate voltages. The values of B_c at each V_g, shown by the arrows, indicate a deviation from the linear behavior at low fields. This enables us to evaluate the spin non-degenerate Fermi energy E_F as $E_F = g\ _B B_c$. The dependence of E_F on V_g is shown in Fig. 2c. We have used a $g = 3.4|g_b|$ for evaluating E_F, where $|g_b| = 0.44$ is the band g-factor in bulk GaAs. This value of g is obtained from V_{SD} measurements, and will be discussed later. Note that above V_g 0.376 V, corresponding to n_s 5 10^8 cm^{-2}, the transport is essentially 2D in nature with E_F varying approximately linearly with V_g. The slope dE_F/dV_g was found to be 12 meV/V, agreeing roughly with the effective free-electron spin non-degenerate 2D density-of-states, $(dE_F/dV_g)_{free} = (\hbar^2/2m)dn_s/dV_g$ $_0\ _r\hbar^2/2em\ d_s$ 16 meV/V, where d_s = 310 nm is the depth of the 2DES from the surface, and m 0.067m_e is the band effective mass of the electron. The discrepancy could be due to a weak density-dependence of g [7]. Below V_g 0.376 V (G 0.3 0.4 $^2e/h$), E_F drops abruptly, possibly due to the onset of inhomogeneity in the charge distribution as screening becomes weak.

The V_{SD} dependence of dI/dV at various values of V_g (i.e., n_s) is shown in Fig. 2a. V_g differs by 1 mV in successive offset-corrected traces. The striking feature of these traces is the double peak structure of dI/dV with a local minimum at V_{SD} = 0. This was found to be a generic feature observed in all the low-disorder samples of similar dimensions. The detection of the double-peak structure was difficult in the strongly localized regime (V_g . 0.385 V), as well as in the metallic regime (V_g & 0.35 V), indicating a disorder-dependent window of n_s where the effect becomes clearly visible. In most cases the peaks are dissimilar in magnitude and width, both of which vary when V_g is changed. The separation ( ) of the peaks shows a non-monotonic dependence on V_g, as shown in Fig. 2b. At low V_g (0.385 V), is largest, but decreases rapidly with increasing V_g, reaching a minimum at V_g 0.375 V. Comparing to the V_g dependence of E_F (Fig. 2c) we find the onset of linear dependence of E_F at the same V_g. When V_g & 0.375 V, increases roughly linearly with increasing V_g. Since this regime can be directly associated with a 2D ground state, we shall restrict further discussions on to this range of V_g. Extrapolating the linear dependence of , we find the V_g (0.395 V) at which = 0, agrees within the experimental uncertainty with the V_g (0.408 V) at which the extrapolated E_F = 0, establishing a direct correspondence between and n_s.

In order to investigate the nature of this effect, we have then studied the double peak structure in a parallel magnetic field. The behavior is illustrated with the trace measured at V_g 0.37 V, indicated by the arrow in Fig. 2b. This is shown in Fig. 3, where the traces with increasing B are vertically offset for clarity. The peak positions (V_p) change non-monotonically as a function of B (see the arrows). We find that the peaks close in over the field scale of B . 0.5 T, but eventually separate at higher fields (see the inset of Fig. 3). The evolution of the peaks with B strongly suggests a spin-related effect, where is the energy difference between the opposite spins. Note that the B-field does not split each peak individually, differentiating our case from a disorder induced quantum molecule. An asymmetrical suppression of the peaks with increasing B sets the maximum field scale (2.8 T) of our experiments, beyond which the left peak becomes undetectable.

The observability and characteristics of the peaks were found to depend critically on disorder and T. We have changed the local disorder profile over the sample region by controlled thermal cycles from room temperature to 4.2 K. The result for three successive thermal cycles carried out for A78 are shown in Fig. 4a. All traces (B and C are shifted vertically for clarity) were recorded at a similar E_F and B = 0. While the general behavior of dI/dV is similar and agrees with that of A79, we find the overall magnitude and width of the peaks to differ markedly, even from one cooling to the other. In general, when the cooling was done at a slow rate (trace A: over a few hours) we found the peaks to be more pronounced than when the cooling was done rapidly (trace C: over few tens of minutes). Greater disorder in C is also observable in terms of the linear response conductance, G 0.1e^2/h, which, in case of A is 0.3e^2/h. Disorder broadening also affects the observability of the effect as the sample dimensions are increased. Typically, no double-peaks were observed in 10 m 10 m samples.

Thermal broadening of the peaks, associated with a strong suppression of the peak height, from T 70 mK to 0.5 K are shown in Fig. 4b. Note that even though G at V_{SD} = 0 rises with increasing T, as expected in a localized system, it is essentially a result of the overlap of the broadening peaks. This also confirms that as a function of V_{SD}, we indeed observe a non-linear effect, and the double peak structure is a ground-state property of the 2D electron system in the low density regime.

We now discuss possible mechanisms which may give rise to such a structure in non-equilibrium measurements. Assuming the formation of a weak tunnel barrier, which physically splits the 2D region in two parts, the conservation of the transverse momentum will allow tunnelling through the barrier only at V_{SD} = 0. This would result in a disorder-broadened ZBP in the tunnelling dI/dV. An interaction-induced suppression of states at E_F, e.g., ln (j j) in the diffusive regime [13] or Efros-Shklovskii-

type soft gap $\quad$ j j in the hopping regime [14], may then spilt the ZBP to give rise to the double peak structure [15]. The main arguments against such a scenario are, (a) the separation of the peaks are B-independent, hence inconsistent with Fig. 3, and (b) the separation decreases with increasing E_F, contrary to the result of Fig. 2b [15].

To investigate if the peak separation $\quad$ is indeed spin-related, we have plotted $\quad$ as a function of B for the data shown in g. 3. As shown in Fig. 5, at low elds $\quad$ decreases with increasing eld, while at high B (& 1 T), shows monotonic increase as B increases. In this high-B regime, $\quad$ tends asymptotically to a linear B dependence (the solid line), which when extrapolated, passes through the origin. This we identify as Zeeman spin splitting. From the asymptote, $_Z = g\ _B B$, we nd g to be $1{:}49 = 3{:}4 j_B j$, agreeing closely to the values reported in recent measurements over similar range of n_s [7]. The peak positions thus represent the energies of two opposite spin states in a magnetic eld, and from the non-zero separation at B = 0, signify a non-zero spin polarization.

From the critical role of spin , and also the behavior of dI=dV near $V_{SD} = 0$, a Kondo-like many-body correlation, as discussed extensively in the context of quantum dots [11], can be envisaged. There are however important di erences. In our system, as in the case of QPC's, there are no obvious singly-occupied quasi-bound electronic states. Unlike the suggested ferromagnetic states in QPC's [16], the magnetic moment of a frozen spin-polarized state in 2D would be much higher than that of a single electron, and hence Kondo-type screening would be di cult. However, as indicated in Fig. 2a for V_g & 0:375 V, the spin-polarization in our system seems to be dynamic, and increases with n_s. This, as suggested for QPC's [17], in presence of optimal band-hybridization, could result in a Kondo-enhanced ZBP in dI=dV. Our case is however further complicated by the splitting of the ZBP at B = 0, resembling the behavior of ZBP in dots and QPC's at a nite B [11, 12]. Although the Kondo e ect in coupled dot systems has a similar non-equilibrium behavior as a function of V_{SD} at B = 0, such a case would appear only over a restricted parameter range of inter-dot and lead couplings, and hence should be rather rare in open systems with no intentional con-nement [18].

Finally, in parallel B, it has been shown that in su -ciently smooth disorder, both SO and exchange-induced spin splitting could result in satellite-peaks in the tunnelling DOS at nite bias $\sqrt{{}_0^2 + {}_Z^2}$, where $_0$ is the magnitude of SSP [19]. The tunnelling DOS could be obtained in a non-linear dI=dV measurement if we assume a quasi-ballistic transport in our clean mesoscopic samples, i.e., electron energies are lost mainly at the leads. Apart from explaining the double-peak structure in dI=dV, this also justi es, (a) broadening of the peaks with disorder and (b) the linear B-dependence of $\quad$ at high B, where $\quad ! \quad _Z$. If $_0$ arises from a strong SO coupling, one expects negative magneto-conductance at low perpendicular B- eld, arising from weak antilocalization. No evidence of antilocalization was observed in our mesoscopic 2D systems. The SO-origin of $_0$ seems to be unlikely on two more grounds. First, calculation of the magnitude of splitting in GaAs/AlGaAs heterostructures, taking into account both bulk and Rashba terms, shows that $_0$ would be 0:05 meV below $n_s \quad 10^{11}$ cm^{-2} [20]. Secondly, if the absence of antilocalization is attributed to a B-dependent $_0$, as in large open quantum dots, $_0$ increases with B at low elds [5, 21]. However, as shown in the inset of Fig. 5, $_0 \quad \sqrt{{}_0^2 \quad {}_Z^2}$ decreases with increasing B in our samples. Alternatively, if we assume that $_0$ arises due to exchange, and in the Fermi liquid limit, represents the shift of one spin state with respect to the other (see the inset of Fig. 5), then an estimate of polarization $\quad$ could be obtained as $= (n_{s"} \quad n_{s\#})/n_s \quad = 2E_F$. In the regime of 2D conduction, V_g & 0:375 V, we nd $\quad$ 0:1, implying only a partial spin polarization. This is probably not surprising considering the low $r_s \quad 6 \quad 7$ in our system, and nite T [3]. The exchange-origin of $_0$ is also supported by the decrease of $_0$ with increasing B, as the additional con nement (B^2) imposed by B tends to counteract the formation of parallel spins [16].

In conclusion, non-linear conductance measurements in high quality mesoscopic 2D electron systems show direct evidence of spontaneous spin polarization at low electron densities. This spin polarization is density-dependent, and manifested by a split zero-bias peak in source-drain bias at B = 0. The peaks are generally asymmetric and strongly depend on the local disorder. Simultaneous measurement of the Fermi energy, and temperature-dependence of conductance con rm the splitting to be an intrinsic property of 2D systems, and also identify a window of electron density and temperature over which the splitting becomes experimentally observable.

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Fig.1

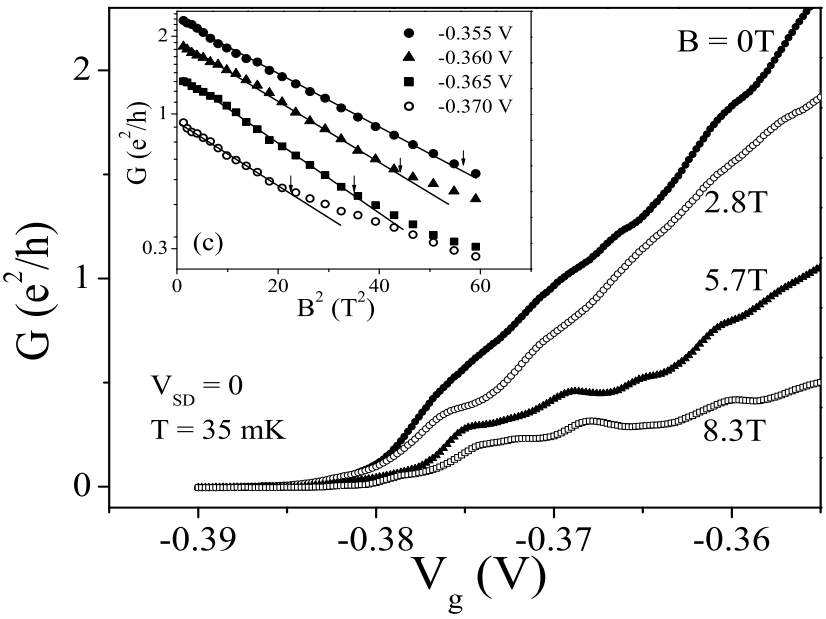

FIG. 1: Typical gate voltage V_g dependence of the linear response conductance G at various magnetic elds. Inset: G, as a function of B^2 at four V_g's. Arrows indicate the deviation from linear dependence, and the onset of complete polarization.

Fig. 2

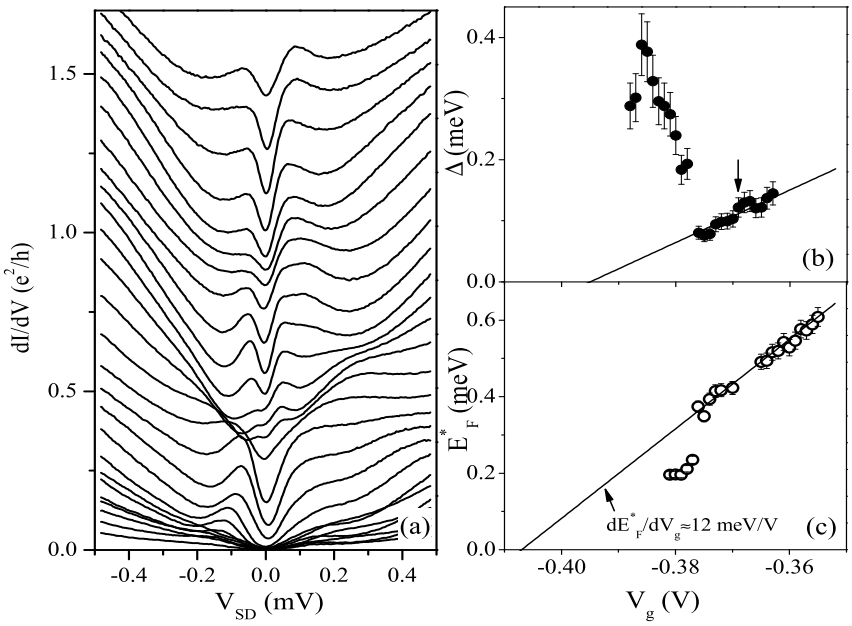

FIG. 2: (a) The differential conductance dI=dV vs. source-drain bias V_{SD} at various V_g. V_g differs by 1 mV for successive sweeps. (b) The peak separation as a function of V_g. (c) V_g-dependence of the spin non-degenerate Fermi energy E_F, obtained from the magnetic eld scale of complete eld polarization (see text).

Fig.3

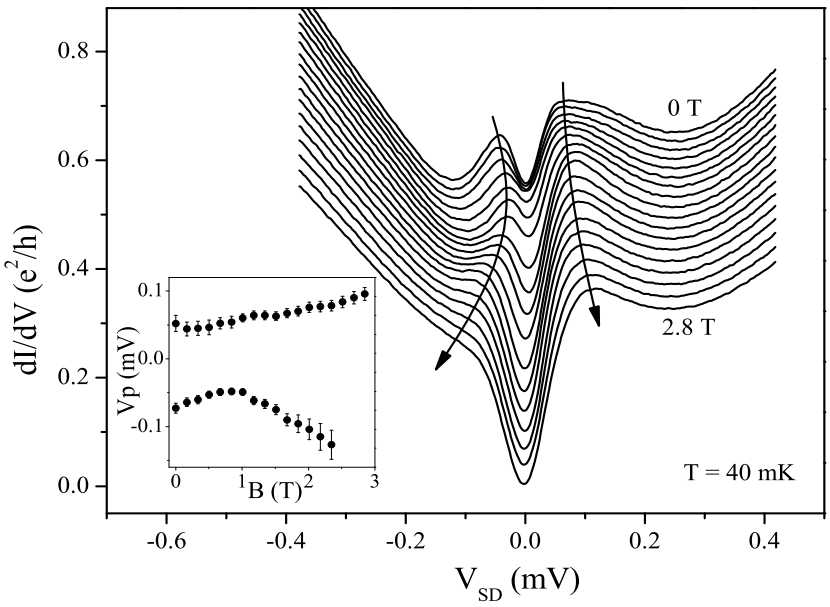

FIG. 3: Evolution of the differential conductance with magnetic field B. We have illustrated this with the trace obtained at V_g 0:37 V (indicated by the arrow in Fig. 2b). Traces are shifted vertically for clarity. Inset: Positions (V_p) of the peaks as a function of B.

Fig. 4

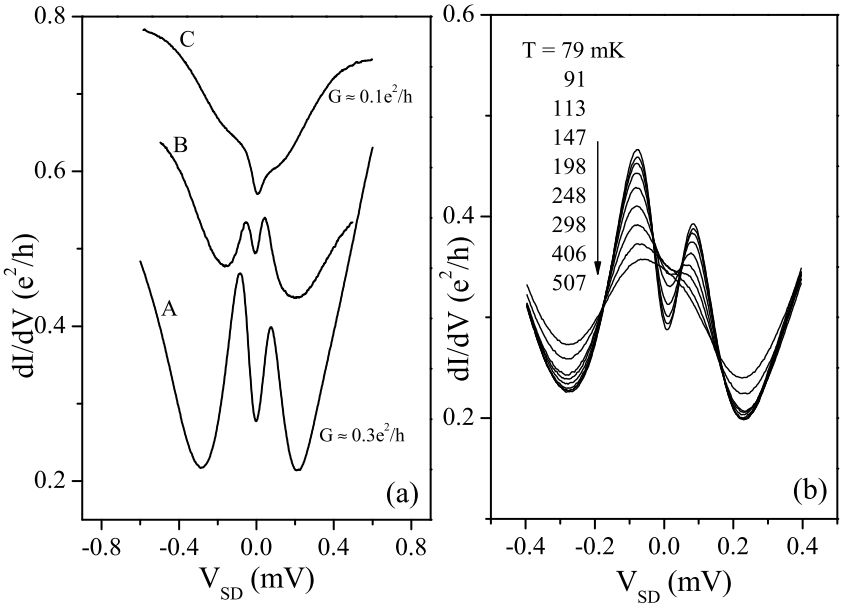

FIG. 4: (a) Double-peak structure in dI=dV in the same sample for various cool-downs. Traces are shifted vertically for easy comparison. The linear response conductance is minimum for C and maximum for A. (b) Temperature dependence of the double peak structure. Note the smearing of each peak results in the increase of the zero-bias conductance with increasing T.

Fig.5

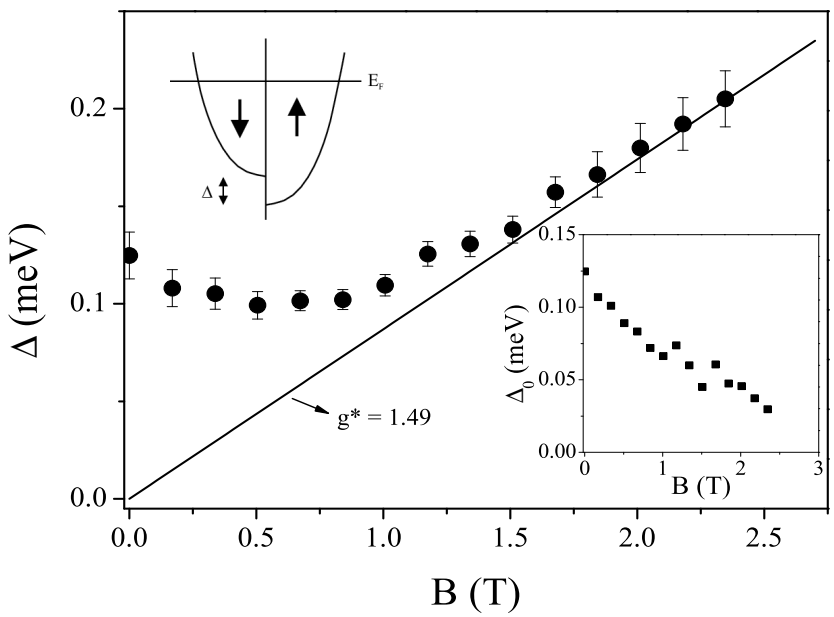

FIG. 5: Dependence of the peak separation on the magnetic eld B. We have used the shown in Fig. 3. The high- eld asymptote extrapolates through the origin. Inset: B-dependence of the $_0$.